The Physics Of Nanoelectronics Transport And Fluctuation Phenomena At Low Temperatures Oxford Master Series In Physics

Nanobiotechnology is a new interdisciplinary science with revolutionary perspectives arising from the fact that at nanosize the behaviour and characteristics of matter change with respect to ordinary macroscopic dimensions. Nanotechnology is a new way for producing and getting materials, structures and devices with greatly improved or completely new properties and functionalities. This book provides an introductory overview of the nanobiotechnology world along with a general technical framework about mathematical modelling through which we today study the phenomena of charge transport at the nanometer level. Although it is not a purely mathematics or physics book, it introduces the basic mathematical and physical notions that are important and necessary for theory and applications in nanobiotechnology. Therefore, it can be considered an extended formulary of basic and advanced concepts. It can be the starting point for discussions and insights and can be used for further developments in mathematical–physical modelling linked to the nanobiotechnology world. The book is dedicated to all those who follow their ideas in life and pursue their choices with determination and firmness, in a free and independent way.

A. Basic concepts. Why electrons flow ; The elastic resistor ; Ballistic and diffusive transport ; Conductance from fluctuation ; Energy band model ; The nanotransistor ; Diffusion equation for ballistic transport ; Boltzmann equation ; Electrochemical potentials and quasi-Fermi levels ; Hall effect ; Smart contacts ; Thermoelectricity ; Phonon transport ; Second law ; Fuel value of information

The second edition offers an update on the single most comprehensive survey of the two intertwined fields of spintronics and magnetism, covering the diverse array of materials and structures, including silicon, organic semiconductors, carbon nanotubes, graphene, and engineered nanostructures. It focuses on seminal pioneering work, together with the latest in cutting-edge advances, notably extended discussion of two-dimensional materials beyond graphene, topological insulators, skyrmions, and molecular spintronics. The main sections cover physical phenomena, spin-dependent tunneling, control of spin and magnetism in semiconductors, and spin-based applications.

Technological advancement in chip development, primarily based on the downscaling of the feature size of transistors, is threatening to come to a standstill as we approach the limits of conventional scaling. For example, when the number of electrons in a device's active region is reduced to less than ten electrons (or holes), quantum fluctuation errors will occur, and when gate insulator thickness becomes too insignificant to block quantum mechanical tunneling, unacceptable leakage will occur. Fortunately, there is truth in the old adage that whenever a *door closes, a window opens somewhere else. In this case, that window opening is nanotechnology. Silicon Nanoelectronics takes a look at at the recent development of novel devices and materials that hold great promise for the creation of still smaller and more powerful chips. Silicon nanodevices are positoned to be particularly relevant in consideration of the existing silicon process infrastructure already in place throughout the semiconductor industry and silicon's consequent compatibility with current CMOS circuits. This is reinforced by the nearly perfect interface that can exist between natural oxide and silicon. Presenting the contributions of more than 20 leading academic and corporate researchers from the United States and Japan, Silicon Nanoelectronics offers a comprehensive look at this emergent technology. The text includes extensive background information on the physics of silicon nanodevices and practical CMOS scaling. It considers such issues as quantum effects and ballistic transport and resonant tunneling in silicon nanotechnology. A significant amount of attention is given to the all-important silicon single electron transistors and the devices that utilize them. In offering an update of the current state-of-the-art in the field of silicon nanoelectronics, this volume serves well as a concise reference for students, scientists, engineers, and specialists in various fields, in*

The Nanotechnology Revolution

Electronic Conduction

Volume Two: Semiconductor Spintronics

Advanced Nanoelectronics

Classical and Quantum Theory to Nanoelectronic Devices

Transport in Semiconductor Mesoscopic Devices

Major developments in the semiconductor industry are on the horizon through the use of two-dimensional (2D) materials, such as graphene and transition metal dichalcogenides, for integrated circuits (ICs). 2D Materials for Nanoelectronics is the first comprehensive treatment of these materials and their applications in nanoelectronic devices. Comprised of chapters authored by internationally recognised researchers, this book: Discusses the use of graphene for high-frequency analog circuits Explores logic and photonic applications of molybdenum disulfide (MoS2) Addresses novel 2D materials including silicene, germanene, stanene, and phosphorene Considers the use of 2D materials for both field-effect transistors (FETs) and logic circuits Provides background on the simulation of structural, electronic, and transport properties from first principles 2D Materials for Nanoelectronics presents extensive, state-of-the-art coverage of the fundamental and applied aspects of this exciting field.

Nanotechnology is changing the world in a very big way, but at the atomic and sub-atomic level. Although the roots of

nanotechnology can be traced back to more than a century ago, the last three decades have witnessed an explosion of nano-based technologies and products. This reference work examines the history, current status, and future directions of nanotechnology through an exhaustive search of the technical and scientific literature. The more than 4000 bibliographic citations it includes are carefully organized into core subject areas, and a geographic and subject index allows readers to quickly locate documents of interest. Although a sense of the global reach and interest in nanotechnology can be gleaned from the reference sections of countless journal articles, conference papers, and books, this is the only reference work providing an in-depth global perspective that is ready-made for nanotechnology professionals and those interested in learning more about all things nanotechnology. Despite the abundance of online resources, there is still an urgent need for well-researched, well-presented, concise, and thematically organized reference works. Instead of relying on wiki pages, citation aggregators, and related websites, the author searched the databases and databanks of scholarly literature search providers such as EBSCO, ProQuest, PUBMED, STN International, and Thomson Reuters. In addition, he used select serials-related databases to account for pertinent documents from countries in which English is not the primary national language (i.e., China Online Journals, e-periodica, J-STAGE, and SciELO Brazil among others).
Nanoelectronics: Devices, Circuits and Systems explores current and emerging trends in the field of nanoelectronics, from both a devices-to-circuits and circuits-to-systems perspective. It covers a wide spectrum and detailed discussion on the field of nanoelectronic devices, circuits and systems. This book presents an in-depth analysis and description of electron transport phenomenon at nanoscale dimensions. Both qualitative and analytical approaches are taken to explore the devices, circuit functionalities and their system applications at deep submicron and nanoscale levels. Recent devices, including FinFET, Tunnel FET, and emerging materials, including graphene, and its applications are discussed. In addition, a chapter on advanced VLSI interconnects gives clear insight to the importance of these nano-transmission lines in determining the overall IC performance. The importance of integration of optics with electronics is elucidated in the optoelectronics and photonic integrated circuit sections of this book. This book provides valuable resource materials for scientists and electrical engineers who want to learn more about nanoscale electronic materials and how they are used. Shows how electronic transport works at the nanoscale level Demonstrates how nanotechnology can help engineers create more effective circuits and systems Assesses the most commonly used nanoelectronic devices, explaining which is best for different situations
Advances in semiconductor technology have made possible the fabrication of structures whose dimensions are much smaller than the mean free path of an electron. This book gives a thorough account of the theory of electronic transport in such mesoscopic systems. After an initial chapter covering fundamental concepts, the transmission function formalism is

presented, and used to describe three key topics in mesoscopic physics: the quantum Hall effect; localisation; and double-barrier tunnelling. Other sections include a discussion of optical analogies to mesoscopic phenomena, and the book concludes with a description of the non-equilibrium Green's function formalism and its relation to the transmission formalism. Complete with problems and solutions, the book will be of great interest to graduate students of mesoscopic physics and nanoelectronic device engineering, as well as to established researchers in these fields.

Quantum Transport

Molecular Electronics

Transport in Nanostructures

Semiconductor-On-Insulator Materials for Nanoelectronics Applications

Semiclassical and Quantum Device Modeling and Simulation

Metrology, Synthesis, Properties and Applications

This book provides an introduction to the physics of nanoelectronics, with a focus on the theoretical aspects of nanoscale devices. The book begins with an overview of the mathematics and quantum mechanics pertaining to nanoscale electronics, to facilitate the understanding of subsequent chapters. It goes on to encompass quantum electronics, spintronics, Hall effects, carbon and graphene electronics, and topological physics in nanoscale devices. Theoretical methodology is developed using quantum mechanical and non-equilibrium Green ' s function (NEGF) techniques to calculate electronic currents and elucidate their transport properties at the atomic scale. The spin Hall effect is explained and its application to the emerging field of spintronics – where an electron ' s spin as well as its charge is utilised – is discussed. Topological dynamics and gauge potential are introduced with the relevant mathematics, and their application in nanoelectronic systems is explained. Graphene, one of the most promising carbon-based nanostructures for nanoelectronics, is also explored. Begins with an overview of the mathematics and quantum mechanics pertaining to nanoscale electronics Encompasses quantum electronics, spintronics, Hall effects, carbon and graphene electronics, and topological physics in nanoscale devices Comprehensively introduces topological dynamics and gauge potential with the relevant mathematics, and extensively discusses their application in nanoelectronic systems

This book provides an introduction to phenomena and models in nanoelectronics. It starts from the basics, but also introduces topics of recent interest, such as superconducting qubits, graphene, and quantum nanoelectromechanics.

Brings the Band Structure of Carbon-Based Devices into the Limelight A shift to carbon is positioning biology as a process of synthesis in mainstream engineering. Silicon is quickly being replaced with carbon-based electronics, devices are being reduced down to nanometer scale, and further potential applications are being considered. While traditionally, engineers are trained by way of physics, chemistry, and mathematics, Nanoelectronics: Quantum Engineering of Low-Dimensional Nanoensembles establishes biology as an essential basic science for engineers to explore. Unifies Science and Engineering: from Quantum Physics to Nanoengineering Drawing heavily on published papers by the author, this research-driven text offers a complete review of nanoelectronic transport starting from quantum waves, to ohmic and ballistic conduction, and saturation-limited extreme nonequilibrium conditions. In addition, it highlights a new paradigm using non-equilibrium Arora ' s Distribution Function (NEADF) and establishes this function as the starting point (from band theory to equilibrium to extreme nonequilibrium carrier statistics). The author focuses on nano-electronic device design and development, including carbon-based devices, and provides you with a vantage point for the global outlook on the future of nanoelectronics devices and ULSI. Encompassing ten chapters, this illuminating text: Converts the electric-field response of drift velocity into current – voltage relationships that are driven by the presence of critical voltage and saturation current arising from the unidirectional drift of carriers Applies the effect of these scaled-down dimensions to nano-MOSFET (metal – oxide – semiconductor field-effect transistor) Considers specialized applications that can be tried through a number of suggested projects that are all feasible with MATLAB ® codes Nanoelectronics: Quantum Engineering of Low-Dimensional Nanoensembles contains the latest research in nanoelectronics, identifies problems and other factors to consider when it comes to nanolayer design and application, and ponders future trends. Print Versions of this book also include access to the ebook version.

As electric devices become smaller and smaller, transport simulations based on the quantum mechanics become more and more important. There are currently numerous textbooks on the basic concepts of quantum transport, but few present calculation methods in detail. This book provides various quantum transport simulation methods and shows applications for transport properties of nanometer-scale systems. It starts with a short review of quantum transport, followed by various calculation methods based on scattering approaches, non-equilibrium Green ' s function (NEGF), master equation, and time-dependent wave-packet diffusion (TD-WPD). With these tools, transport properties of various nanosystems are then explored.

A New Perspective on Transport

Perspectives from Physics, Chemistry, and Biology

Introduction to the Physics of Nanoelectronics

An Introduction to Quantum Transport in Semiconductors

Nanostructures and Nanotechnology

An Introduction

Transport Phenomena in Micro- and Nanoscale Functional Materials and Devices offers a pragmatic view on transport phenomena for micro- and nanoscale materials and devices, both as a research tool and as a means to implant new functions in materials. Chapters emphasize transport properties (TP) as a research tool at the micro/nano level and give an experimental view on underlying techniques. The relevance of TP is highlighted through the interplay between a micro/nanocarrier's characteristics and media characteristics: long/short-range order and disorder excitations, couplings, and in energy conversions. Later sections contain case studies on the role of transport properties in functional nanomaterials. This includes transport in thin films and nanostructures, from nanogranular films, to graphene and 2D semiconductors and spintronics, and from read heads, MRAMs and sensors, to nano-oscillators and energy conversion, from figures of merit, micro-coolers and micro-heaters, to spincaloritronics. Presents a pragmatic description of electrical transport phenomena in micro- and nanoscale materials and devices from an experimental viewpoint Provides an in-depth overview of the experimental techniques available to measure transport phenomena in micro- and nanoscale materials Features case studies to illustrate how each technique works Highlights emerging areas of interest in micro- and nanomaterial transport phenomena, including spintronics

Charge migration through DNA has been the focus of considerable interest in recent years. This book presents contributions from an international team of researchers active in this field. It contains a wide range of topics that includes the mathematical background of the quantum processes involved, the role of charge transfer in DNA radiation damage, a new approach to DNA sequencing, DNA *photonics, and many others.*

Rapid developments in technology have led to enhanced electronic systems and applications. When utilized correctly, these can have significant impacts on communication and computer systems. Transport of Information-Carriers in Semiconductors and Nanodevices is an innovative source of academic material on transport modelling in semiconductor material and nanoscale devices. Including a range of perspectives on relevant topics such as charge carriers, semiclassical transport theory, and organic semiconductors, this is an ideal publication for engineers, researchers, academics, professionals, and practitioners interested in emerging developments on transport equations that govern information carriers.

This book presents the conceptual framework underlying the atomistic theory of matter, emphasizing those aspects that relate to current flow. This includes some of the most advanced concepts of non-equilibrium quantum statistical mechanics. No prior acquaintance with quantum mechanics is assumed. Chapter 1 provides a description of quantum transport in elementary terms accessible to a beginner. The book then works its way from hydrogen to nanostructures, with extensive coverage of current flow. The final chapter summarizes the equations for quantum transport with illustrative examples showing how conductors evolve from the atomic to the ohmic regime as they get larger. Many numerical examples are used to provide concrete illustrations and the corresponding Matlab codes can be downloaded from the web. Videostreamed lectures, keyed to specific sections of the book, are also available through the web. This book is primarily aimed at senior and graduate students.

Introduction to Nanoelectronics

Quantum Transport Calculations for Nanosystems

Nonequilibrium Quantum Transport Physics in Nanosystems

The Physics of Nanoelectronics

Foundation of Computational Nonequilibrium Physics in Nanoscience and Nanotechnology

From Electronic Structure to Quantum Transport

Everyone is familiar with the amazing performance of a modern smartphone, powered by a billion-plus nanotransistors, each having an active region that is barely a few hundred atoms long. The same amazing technology has also led to a deeper understanding of the nature of current flow and heat dissipation on an atomic scale which is of broad relevance to the general problems of non-equilibrium statistical mechanics that pervade many different fields.This book is based on a set of two online courses originally offered in 2012 on nanoHUB-U and more recently in 2015 on edX. In preparing the second edition the author decided to split it into parts A and B titled Basic Concepts and Quantum Transport respectively, along the lines of the two courses. A list of available video lectures corresponding to different sections of this volume is provided upfront.To make these lectures accessible to anyone in any branch of science or engineering, the author assume very little background beyond linear algebra and differential equations. However, the author will be discussing advanced concepts that should be of interest even to specialists, who are encouraged to look at his earlier books for additional technical details.

Basic concepts -- Distribution functions -- The Lorentz model for the classical transport of charges -- The Boltzmann equation for dilute gases -- Brownian motion -- Plasmas and self-gravitating systems -- Quantum gases -- Quantum electronic transport in solids -- Semiconductors and interband transitions -- Numerical and semianalytical methods.

This book is aimed at senior undergraduates, graduate students and researchers interested in quantitative understanding and modeling of nanomaterial and device physics. With the rapid slow-down of semiconductor scaling that drove information technology for decades, there is a pressing need to understand and model electron flow at its fundamental molecular limits. The purpose of this book is to enable such a deconstruction needed to design the next generation memory, logic, sensor and communication elements. Through numerous case studies and topical examples relating to emerging technology, this book connects 'top down' classical device physics taught in electrical engineering classes with 'bottom up' quantum and many-body transport physics taught in physics and chemistry. The book assumes no more than a nodding acquaintance with quantum mechanics, in addition to knowledge of freshman level mathematics. Segments of this book are useful as a textbook for a course in nano-electronics.

This book covers the state of the art in the theoretical framework, computational modeling, and the fabrication and characterization of nanoelectronics devices. It addresses material properties, device physics, circuit analysis, system design, and a range of applications. A discussion on the nanoscale fabrication, characterization and metrology is also included. The book offers a valuable resource for researchers, graduate students, and senior undergraduate students in engineering and natural sciences, who are interested in exploring nanoelectronics from materials, devices, systems, and applications perspectives.

Theory of Quantum Transport at Nanoscale

A Global Bibliographic Perspective

Electronic Transport in Mesoscopic Systems

Introduction to Graphene-Based Nanomaterials

Lessons From Nanoelectronics: A New Perspective On Transport (Second Edition) - Part B: Quantum Transport

A Molecular View

Graphene is one of the most intensively studied materials, and has unusual electrical, mechanical and thermal properties, which provide almost unlimited potential applications. This book provides an introduction to the electrical and transport properties of graphene and other two dimensional nanomaterials, covering ab-initio to multiscale methods. Updated from the first edition, the authors have added chapters on other two dimensional materials, spin related phenomena, and an improved overview of Berry phase effects. Other topics include powerful order N electronic structure, transport calculations, ac transport and multiscale transport methodologies. Chapters are complemented with concrete examples and case studies, questions and exercises, detailed appendices and computational codes. It is a valuable resource for graduate students and researchers working in physics, materials science or engineering who are interested in the field of graphene-based nanomaterials.

Modern electronics is being transformed as device size decreases to a size where the dimensions are *significantly smaller than the constituent electron's mean free path. In such systems the electron motion is strongly confined resulting in dramatic changes of behaviour compared to the bulk. This book introduces the physics and applications of transport in such mesoscopic and nanoscale electronic systems and devices. The behaviour of these novel devices is influenced by numerous effects not seen in bulk semiconductors, such as the Aharonov-Bohm Effect, disorder and localization, energy quantization, electron wave interference, spin splitting, tunnelling and the quantum hall effect to name a few. Including coverage of recent developments, and with a chapter on carbon-based nanoelectronics, this book will provide a good course text for advanced students or as a handy reference for researchers or those entering this interdisciplinary area.*

A carefully developed textbook focusing on the fundamental principles of nanoscale science and nanotechnology.

The advent of semiconductor structures whose characteristic dimensions are smaller than the mean free path of carriers has led to the development of novel devices, and advances in theoretical understanding of mesoscopic systems or nanostructures. This book has been thoroughly revised and provides a much-needed update on the very latest experimental research into mesoscopic devices and develops a detailed theoretical framework for understanding their behaviour. Beginning with the key observable phenomena in nanostructures, the authors describe quantum confined systems, transmission in nanostructures, quantum dots, and single electron phenomena. Separate chapters are devoted to interference in diffusive transport, temperature decay of fluctuations, and non-equilibrium transport and nanodevices. Throughout the book, the authors interweave experimental results with the appropriate theoretical formalism. The book will be of great interest to graduate students taking courses in mesoscopic physics or nanoelectronics, and researchers working on semiconductor nanostructures.

Charge Migration in DNA

2D Materials for Nanoelectronics

Computational Electronics

Kinetic Theory and Transport Phenomena

Nanoelectronics

Electronic Conduction: Classical and Quantum Theory to Nanoelectronic Devices provides a concise, complete introduction to the fundamental principles of electronic conduction in microelectronic and nanoelectronic devices, with an emphasis on integrating the quantum aspects of conduction. The chapter coverage begins by presenting the classical theory of conduction, including introductory chapters on quantum mechanics and the solid state, then moving to a complete presentation of essential theory for understanding modern electronic devices. The author ' s unique approach is applicable to microscale and nanoscale device simulation, which is particularly timely given the explosion in the nanoelectronics field. Features Self-contained Gives a complete account of classical and quantum aspects of conduction in nanometer scale devices Emphasises core principles, the book can be useful to electrical engineers and material scientists, and no prior course in semiconductors is necessary Highlights the bridge to modern electronics, first presenting the physics, and then the engineering complications related to quantum behaviour Includes many clear, illustrative diagrams and chapter problem sets Gives an account of post-Silicon devices such as the GaAs MOSFET, the CNT-FET and the vacuum transistor Showcases why quantum mechanics is necessary with modern devices due to their size and corresponding electron transport properties Discusses all the issues that will enable readers to conduct their own research

Graphene is a perfectly two-dimensional single-atom thin membrane with zero bandgap. It has attracted huge attention due to its linear dispersion around the Dirac point, excellent transport properties, novel magnetic characteristics, and low spin-orbit coupling. Graphene and its nanostructures may have potential applications in spintronics, photonics, plasmonics and electronics. This book brings together a team of experts to provide an overview of the most advanced topics in theory, experiments, spectroscopy and applications of graphene and its nanostructures. It covers the state-of-the-art in tutorial-like and review-like manner to make the book useful not only to experts, but also newcomers and graduate students.

"Semiconductor-On-Insulator Materials for NanoElectronics Applications ” is devoted to the fast evolving field of modern nanoelectronics, and more particularly to the physics and technology of nanoelectronic devices built on semiconductor-on-insulator (SemOI) systems. The book contains the achievements in this field from leading companies and universities in Europe, USA, Brazil and Russia. It is articulated around four main topics: 1. New semiconductor-on-insulator materials; 2. Physics of modern SemOI devices; 3. Advanced characterization of SemOI devices; 4. Sensors and MEMS on SOI. "Semiconductor-On-Insulator Materials for NanoElectonics Applications ” is useful not only to specialists in nano- and microelectronics but also to students and to the wider audience of readers who are interested in new directions in modern electronics and optoelectronics.

While theories based on classical physics have been very successful in helping experimentalists design microelectronic devices, new approaches based on quantum mechanics are required to accurately model nanoscale transistors and to predict their characteristics even before they are fabricated. Advanced Nanoelectronics provides research information on advanced nanoelectronics concepts, with a focus on modeling and simulation. Featuring contributions by researchers actively engaged in nanoelectronics research, it develops and applies analytical formulations to investigate nanoscale devices. The book begins by introducing the basic ideas related to quantum theory that are needed to better understand nanoscale structures found in nanoelectronics, including graphenes, carbon nanotubes, and quantum wells, dots, and wires. It goes on to highlight some of the key concepts required to understand nanotransistors. These concepts are then applied to the carbon nanotube field effect transistor (CNTFET). Several chapters cover graphene, an unzipped form of CNT that is the recently discovered allotrope of carbon that has gained a tremendous amount of scientific and technological interest. The book discusses the development of the graphene nanoribbon field effect transistor (GNRFET) and its use as a possible replacement to overcome the CNT chirality challenge. It also examines silicon nanowire (SiNW) as a new candidate for achieving the downscaling of devices. The text describes the modeling and fabrication of SiNW, including a new top-down fabrication technique. Strained technology, which changes the properties of device materials rather than changing the device geometry, is also discussed. The book ends with a look at the technical and economic challenges that face the commercialization of nanoelectronics and what universities, industries, and government can do to lower the barriers. A useful resource for professionals, researchers, and scientists, this work brings together state-of-the-art technical and scientific information on important topics in advanced nanoelectronics.

Devices, Circuits and Systems

Transport Phenomena in Micro- and Nanoscale Functional Materials and Devices

Silicon Nanoelectronics

Nanoelectronics Fundamentals

An Introduction to Theory and Experiment

Transport and Fluctuation Phenomena at Low Temperatures

Textbook presenting the fundamentals of nanoscience and nanotechnology with a view to nanoelectronics. Covers the underlying physics; nanostructures, including nanoobjects; methods for growth, fabrication and characterization of nanomaterials; and nanodevices. Provides a unifying framework for the basic ideas needed to understand the recent developments in the field. Includes numerous illustrations, homework problems and a number of interactive Java applets. For advanced undergraduate and graduate students in electrical and electronic engineering, nanoscience, materials, bioengineering and chemical engineering. Instructor solutions and Java applets available from www.cambridge.org/9780521881722.

This book is an introduction to a rapidly developing field of modern theoretical physics the theory of quantum transport at nanoscale. The theoretical methods considered in the book are in the basis of our understanding of charge, spin and heat transport in nanostructures and nanostructured materials and are widely used in nanoelectronics, molecular electronics, spin-dependent electronics (spintronics) and bio-electronics. The book is based on lectures for graduate and post-graduate students at the University of Regensburg and the Technische Universität Dresden (TU Dresden). The first part is devoted to the basic concepts of quantum transport: Landauer-Büttiker method and matrix Green function formalism for coherent transport, Tunneling (Transfer) Hamiltonian and master equation methods for tunneling, Coulomb blockade, vibrons and polarons. The results in this part are obtained as possible without sophisticated techniques, such as nonequilibrium Green functions, which are considered in detail in the second part. A general introduction into the nonequilibrium Green function theory is given. The approach based on the equation-of-motion technique, as well as more sophisticated one based on the Dyson-Keldysh diagrammatic technique are presented. The main attention is paid to the theoretical methods able to describe the nonequilibrium (at finite voltage) electron transport through interacting nanosystems, specifically the correlation effects due to electron-electron and electron-vibron interactions.

This textbook is aimed at second-year graduate students in Physics, Electrical Engineering, or Materials Science. It presents a rigorous introduction to electronic transport in solids, especially at the nanometer scale.Understanding electronic transport in solids requires some basic knowledge of Hamiltonian Classical Mechanics, Quantum Mechanics, Condensed Matter Theory, and Statistical Mechanics. Hence, this book discusses those sub-topics which are required to deal with electronic transport in a single, self-contained course. This will be useful for students who intend to work in academia or the nano/ micro-electronics industry.Further topics covered include: the theory of energy bands in crystals, of second quantization and elementary excitations in solids, of the dielectric properties of semiconductors with an emphasis on dielectric screening and coupled interfacial modes, of electron scattering with phonons, plasmons, electrons and photons, of the derivation of transport equations in semiconductors and semiconductor nanostructures somewhat at the quantum level, but mainly at the semi-classical level. The text presents examples relevant to current research, thus not only about Si, but also about III-V compound semiconductors, nanowires, graphene and graphene nanoribbons. In particular, the text gives major emphasis to plane-wave methods applied to the electronic structure of solids, both DFT and empirical pseudopotentials, always paying attention to their effects on electronic transport and its numerical treatment. The core of the text is electronic transport, with ample discussions of the transport equations derived both in the quantum picture (the Liouville-von Neumann equation) and semi-classically (the Boltzmann transport equation, BTE). An advanced chapter, Chapter 18, is strictly related to the tricky transition from the time-reversible Liouville-von Neumann equation to the time-irreversible Green's functions, to the density-matrix formalism and, classically, to the Boltzmann transport equation. Finally, several methods for solving the BTE are also reviewed, including the method of moments, iterative methods, direct matrix inversion, Cellular Automata and Monte Carlo. Four appendices complete the text.

Advances in nanotechnology have allowed physicists and engineers to miniaturize electronic structures to the limit where finite-size related phenomena start to impact their properties. This book discusses such phenomena and models made for their description. The book starts from the semiclassical description of nonequilibrium effects, details the scattering theory used for quantum transport calculations, and explains the main interference effects. It also describes how to treat fluctuations and correlations, how interactions affect transport through small islands, and how superconductivity modifies these effects. The last two chapters describe new emerging fields related with graphene and nanoelectromechanics. The focus of the book is on the phenomena rather than formalism, but the book still explains in detail the main models constructed for these phenomena. It also introduces a number of electronic devices, including the single-electron transistor, the superconducting tunnel junction refrigerator, and the superconducting quantum bit.

Spintronics Handbook, Second Edition: Spin Transport and Magnetism

Graphene Nanoelectronics

Transport of Information-Carriers in Semiconductors and Nanodevices

Lessons From Nanoelectronics: A New Perspective On Transport (Second Edition) - Part A: Basic Concepts

Quantum Engineering of Low-Dimensional Nanoensembles

Science, Nanotechnology, Engineering, and Applications

Throughout their college career, most engineering students have done problems and studies that are basically situated in the classical world. Some may have taken quantum mechanics as their chosen field of study. This book moves beyond the basics to highlight the full quantum mechanical nature of the transport of carriers through nanoelectronic structures. The book is unique in that addresses quantum transport only in the materials that are of interest to microelectronics—semiconductors, with their variable densities and effective masses. The author develops Green's functions starting from equilibrium Green's functions and going through modern time-dependent approaches to non-equilibrium Green's functions, introduces relativistic bands for graphene and topological insulators and discusses the quantum transport changes that these bands induce, and discusses applications such as weak localization and phase breaking processes, resonant tunneling diodes, single-electron tunneling, and entanglement. Furthermore, he also explains modern ensemble Monte Carlo approaches to simulation of various approaches to quantum transport and the hydrodynamic approaches to quantum transport. All in all, the book describes all approaches to quantum transport in semiconductors, thus becoming an essential textbook for advanced graduate students in electrical engineering or physics.

The Physics of NanoelectronicsTransport and Fluctuation Phenomena at Low TemperaturesOxford University Press

This book provides a comprehensive overview of the rapidly developing field of molecular electronics. It focuses on our present understanding of the electrical conduction in single-molecule circuits and provides a thorough introduction to the experimental techniques and theoretical concepts. It will also constitute as the first textbook-like introduction to both the experiment and theory of electronic transport through single atoms and molecules. In this sense, this publication will prove invaluable to both researchers and students interested in the field of nanoelectronics and nanoscience in general. Molecular Electronics is self-contained and unified in its presentation. It may be used as a textbook on nanoelectronics by graduate students and advanced undergraduates studying physics and chemistry. In addition, included are previously unpublished material that will help researchers gain a deeper understanding into the basic concepts involved in the field of molecular electronics.

Transport Phenomena in Micro- and Nanoscale Functional Materials and Devices offers a pragmatic view on transport phenomena for micro- and nanoscale materials and devices, both as a research tool and as a means to implant new functions in materials. Chapters emphasize transport properties (TP) as a research tool at the micro/nano level and give an experimental view on underlying techniques. The relevance of TP is highlighted through the interplay between a micro/nanocarrier's characteristics and media characteristics: long/short-range order and disorder excitations, couplings, and in energy conversions. Later sections contain case studies on the role of transport properties in functional nanomaterials. This includes transport in thin films and nanostructures, from nanogranular films, to graphene and 2D *semiconductors and spintronics, and from read heads, MRAMs and sensors, to nano-oscillators and energy conversion, from figures of merit, micro-coolers and micro-heaters, to spincaloritronics. Presents a pragmatic description of electrical transport phenomena in micro- and nanoscale materials and devices from an experimental viewpoint Provides an in-depth overview of the experimental techniques available to measure transport phenomena in micro- and nanoscale materials Features case studies to illustrate how each technique works Highlights emerging areas of interest in micro- and nanomaterial transport phenomena, including spintronics*

Lessons from Nanoelectronics

Materials, Devices and Systems

Physical Theory and Device Analysis

Introductory Nanoelectronics

Advanced Physics of Electron Transport in Semiconductors and Nanostructures

Technical Tools and Modelling

This introductory text develops the reader's fundamental understanding of core principles and experimental aspects underlying the operation of nanoelectronic devices. The author makes a thorough and systematic presentation of electron transport in quantum-confined systems such as quantum dots, quantum wires, and quantum wells together with Landauer-Büttiker formalism and non-equilibrium Green's function approach. The coverage encompasses nanofabrication techniques and characterization tools followed by a comprehensive exposition of nanoelectronic devices including resonant tunneling diodes, nanoscale MOSFETs, carbon nanotube FETs, high-electron-mobility transistors, single-electron transistors, and heterostructure optoelectronic devices. The writing throughout is simple and straightforward, with clearly drawn illustrations and extensive self-study exercises for each chapter. Introduces the basic concepts underlying the operation of nanoelectronic devices. Offers a broad overview of the field, including state-of-the-art developments. Covers the relevant quantum and solid-state physics and nanoelectronic device principles. Written in lucid language with accessible mathematical treatment. Includes extensive end-of-chapter exercises and many insightful diagrams.

Written by one of the founders of this field, this book provides a historical overview of the invention of superlattice, one of the most important devices of the second half of the twentieth century. In addition to describing the fundamental concepts, this completely revised and updated edition provides new insights in the field of man-made solids. Written by one of the founders of this field Delivers over 20% new material, including new research and new technological applications Provides a basic understanding of the physics involved from first principles, while adding new depth, using basic mathematics and an explanation of the background essentials

Starting with the simplest semiclassical approaches and ending with the description of complex fully quantum-

mechanical methods for quantum transport analysis of state-of-the-art devices, Computational Electronics: Semiclassical and Quantum Device Modeling and Simulation provides a comprehensive overview of the essential techniques and methods for effectively analyzing transport in semiconductor devices. With the transistor reaching its limits and new device designs and paradigms of operation being explored, this timely resource delivers the simulation methods needed to properly model state-of-the-art nanoscale devices. The first part examines semiclassical transport methods, including drift-diffusion, hydrodynamic, and Monte Carlo methods for solving the Boltzmann transport equation. Details regarding numerical implementation and sample codes are provided as templates for sophisticated simulation software. The second part introduces the density gradient method, quantum hydrodynamics, and the concept of effective potentials used to account for quantum-mechanical space quantization effects in particle-based simulators. Highlighting the need for quantum transport approaches, it describes various quantum effects that appear in current and future devices being mass-produced or fabricated as a proof of concept. In this context, it introduces the concept of effective potential used to approximately include quantum-mechanical space-quantization effects within the semiclassical particle-based device simulation scheme. Addressing the practical aspects of computational electronics, this authoritative resource concludes by addressing some of the open questions related to quantum transport not covered in most books. Complete with self-study problems and numerous examples throughout, this book supplies readers with the practical understanding required to create their own simulators.

Atom to Transistor

Mathematics and Physics for Nanotechnology

Superlattice to Nanoelectronics